PbS near-infrared detector Multi-Pixel thin-film encapsulated



Features

- Bondable electrode for COB mounting
- High durability for rugged operation
- Very high sensitivity
- Suitable for automated wire-bonding
- Room temperature operation

Applications

- Spectroscopy
- Gas detection and analysis
- Flame monitoring
- Flame and spark detection
- Temperature measurement
- Moisture measurement

Electrical and optical characteristics per pixel

Element	Peak wave-	20% cut-off	Peak D*		Time constant	Dark resistance R _D
temperature	length λ₽	wavelength λ_{C}	(620 Hz, 1 Hz)		[µs]	[MΩ]
[°C]	[µm]	[µm]	[cm·Hz ^½ /W]			
	Тур.	Тур.	Тур.	Min.	Тур.	
22	2.7	2.9	1 · 10 ¹¹	$0.5 \cdot 10^{11}$	200	0.3 - 15*

^{*}depends on pixel geometry

- Measured with 1550 nm LED, incident power 16 μW/cm²
- Measured in a voltage divider circuit with 50 V/mm
- Photo responsivity and detectivity are measured with constant load resistance ($R_L = 1 \text{ M}\Omega$) and calculated for matched resistance

Possible mechanical characteristics

Number of lines 1 - 4
 Number of pixels 2 - 16
 Minimum pixel width 20 μm
 Minimum pixel height 20 μm
 Minimum pixel pitch 50 μm
 Minimal chip length 3000 μm
 Minimal chip height 3000 μm

Please contact us for an individual design: info@hertzstueck.de

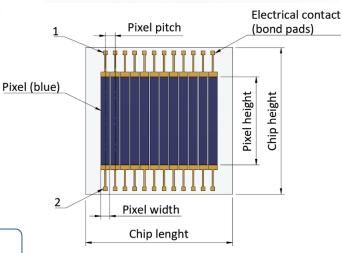
Schematic



- 1 Electrode 1
- (2) Electrode 2







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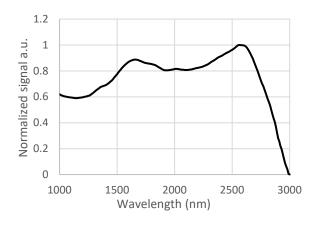


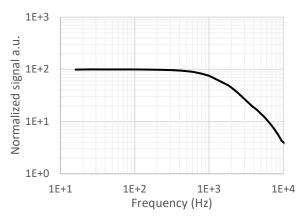
A brand of BASF – We create chemistry

Exemplary mechanical characteristics

Type No.	Number	Number	Pixel	Pixel	Pixel	Operating
	of lines	of pixels	pitch	width	height	temperature
			[µm]	[µm]	[µm]	[°C]
PbS_MP_01x12_0200_0180x1800	1	12	200	180	x 1800	-30 to +70

Typical spectral response per pixel Typical frequency response per pixel





Die attach

- Use clean, soft rubber tip for pick and place handling
- UV-curing is not suitable due to permanent damage by UV light exposure
- Element temperature should never exceed +70°C

Wire-bonding

- Electrodes are optimized for room temperature Al-wire-bonding
- Element temperature should never exceed +70°C

Storage

- Storage temperature: -55°C to +70°C
- Exposure to UV light results in permanent damage
- Prolonged exposure to visible light results in temporary low dark resistance

Handling

- Active area is scratch sensitive, protect top surface from any mechanical contact
- Ensure dust-free environment for device handling
- Operating temperature: -30°C to +70°C

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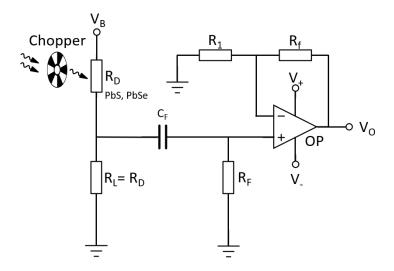
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Options

- Individual housing
- Bonding onto PCB
- Integrated optics
- Evaluation-Kit available

Exemplary circuit



V_B: Bias voltage

V₀: Output voltage

R_D: Dark resistance of the detector

R_L: Load resistor
 C_F: Filter capacitor
 R_F: Filter resistor
 R_f: Feedback resistor

R₁: Gain resistor

Regulatory

For the use of Hertzstück™ PbS and PbSe infrared photodetectors in medical devices, monitoring and control instruments and consumer applications RoHS exemptions apply.

For automotive applications Hertzstück™ PbS and PbSe infrared photodetectors fall under ELV exemption.

